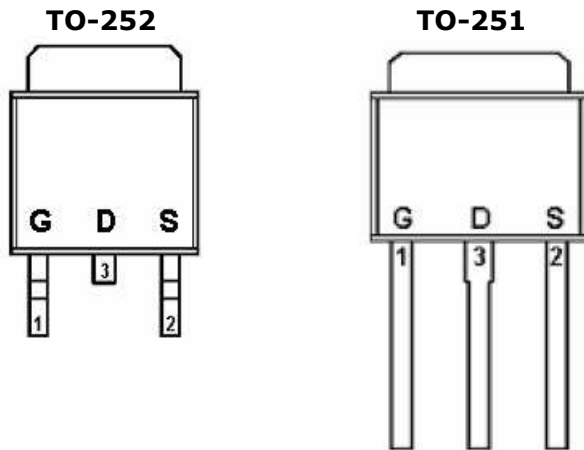
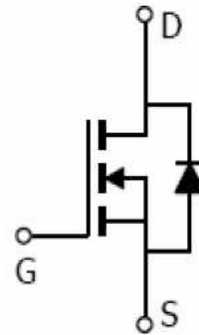
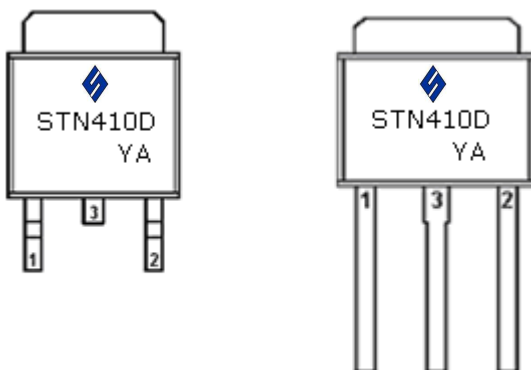


**DESCRIPTION**

STN410D is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. The STN410D has been designed specially to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

**PIN CONFIGURATION (D-PAK)**

**FEATURE**

- 30V/ 15.0A,  $R_{DS(ON)} = 40m\Omega$   
@ $V_{GS} = 10V$
- 30V/8.0A,  $R_{DS(ON)} = 50m\Omega$   
@ $V_{GS} = 4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-252, TO-251 package design

**PART MARKING**


**Y: Year Code A: Process Code**



**STN410D**



N Channel Enhancement Mode MOSFET

15.0A

**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C Unless otherwise noted )

| Parameter                                    | Symbol | Typical         | Unit |
|--|--------|-----------------|------|
| Drain-Source Voltage                         | VDSS   | 30              | V    |
| Gate-Source Voltage                          | VGSS   | ±12             | V    |
| Continuous Drain Current<br>(TJ=150°C)       | ID     | TA=25°C<br>15.0 | A    |
|  |        | TA=70°C<br>10.0 |      |
| Pulsed Drain Current                         | IDM    | 30              | A    |
| Continuous Source Current (Diode Conduction) | IS     | 12              | A    |
| Power Dissipation                            | PD     | TA=25°C<br>25   | W    |
|  |        | TA=70°C<br>12.5 |      |
| Operation Junction Temperature               | TJ     | 150             | °C   |
| Storage Temperature Range                    | TSTG   | -55/150         | °C   |
| Thermal Resistance-Junction to Ambient       | RθJA   | 60              | °C/W |



**STN410D**



N Channel Enhancement Mode MOSFET

15.0A

**ELECTRICAL CHARACTERISTICS** ( Ta = 25°C Unless otherwise noted )

| Parameter                       | Symbol                | Condition   | Min | Typ  | Max       | Unit |
|---------------------------------|-----------------------|---|-----|------|-----------|------|
| <b>Static</b>                   |                       |   |     |      |           |      |
| Drain-Source Breakdown Voltage  | $V_{(BR)DSS}$         | $V_{GS}=0V, I_D=250\mu A$                         | 30  |      |           | V    |
| Gate Threshold Voltage          | $V_{GS(th)}$          | $V_{DS}=V_{GS}, I_D=250\mu A$                     | 0.6 |      | 1.6       | V    |
| Gate Leakage Current            | $I_{GSS}$             | $V_{DS}=0V, V_{GS}=\pm 12V$                       |     |      | $\pm 100$ | nA   |
| Zero Gate Voltage Drain Current | $I_{DSS}$             | $V_{DS}=24V, V_{GS}=0V$                           |     |      | 1         | uA   |
|                                 |                       | $V_{DS}=24V, V_{GS}=0V$<br>$T_J=85^\circ C$       |     |      | 5         |      |
| On-State Drain Current          | $I_{D(on)}$           | $V_{DS} \geq 5V, V_{GS}=4.5V$                     | 30  |      |           | A    |
| Drain-source On-Resistance      | $R_{DS(on)}$          | $V_{GS}=10V, I_D=15.0A$                           |     | 30   | 40        | mΩ   |
|                                 |                       | $V_{GS}=4.5V, I_D=8.0A$                           |     | 36   | 50        |      |
| Forward Transconductance        | $g_{fs}$              | $V_{DS}=5V, I_D=12A$                              |     | 20   |           | S    |
| Diode Forward Voltage           | $V_{SD}$              | $I_S=1.0A, V_{GS}=0V$                             |     |      | 1.2       | V    |
| <b>Dynamic</b>                  |                       |   |     |      |           |      |
| Total Gate Charge               | $Q_g$                 | $V_{DS}=10V, V_{DS}=15V$<br>$I_D=8A$              |     | 7    |           | nC   |
| Gate-Source Charge              | $Q_{gs}$              |   |     | 3.4  |           |      |
| Gate-Drain Charge               | $Q_{gd}$              |   |     | 1.78 |           |      |
| Input Capacitance               | $C_{iss}$             | $V_{DS} = 15V, V_{DS}=15V$<br>$F=1MHz$            |     | 290  |           | pF   |
| Output Capacitance              | $C_{oss}$             |   |     | 60   |           |      |
| Reverse Transfer Capacitance    | $C_{rss}$             |   |     | 75   |           |      |
| Turn-On Time                    | $t_{d(on)}$<br>$t_r$  | $V_{DD}=10V, R_L= 1.8\Omega$<br>$V_{GEN}=3\Omega$ |     | 4    |           | nS   |
|                                 |                       |   |     | 3.7  |           |      |
| Turn-Off Time                   | $t_{d(off)}$<br>$t_f$ |   |     | 15.9 |           |      |
|                                 |                       |   |     | 2.6  |           |      |

**TYPICAL CHARACTERISTICS**

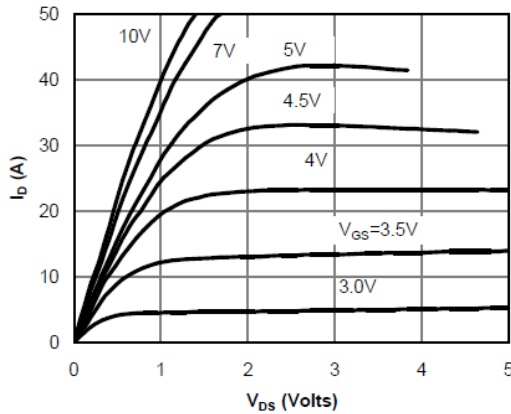


Fig 1: On-Region Characteristics

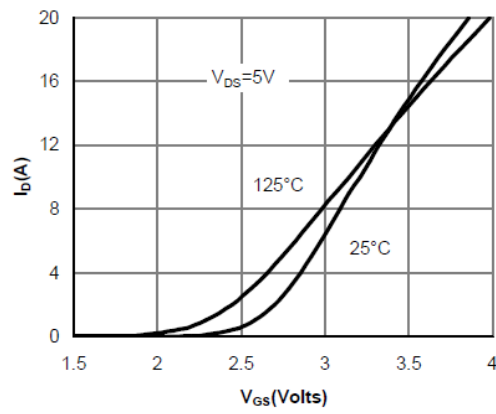


Figure 2: Transfer Characteristics

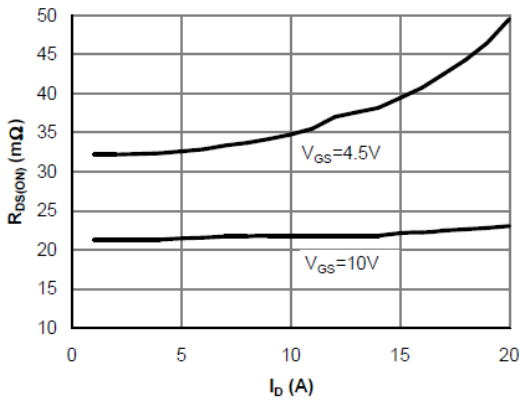


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

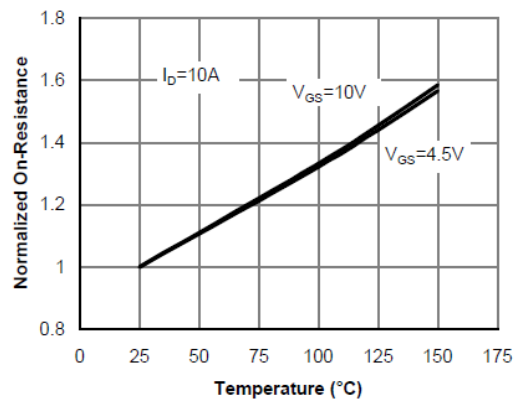


Figure 4: On-Resistance vs. Junction Temperature

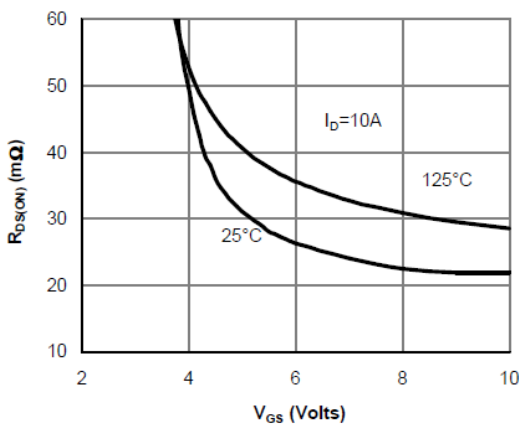


Figure 5: On-Resistance vs. Gate-Source Voltage

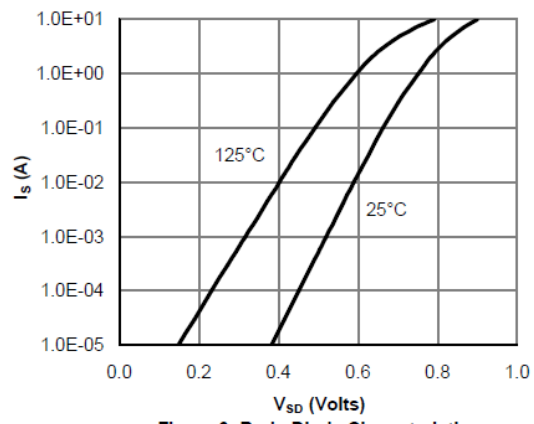


Figure 6: Body-Diode Characteristics

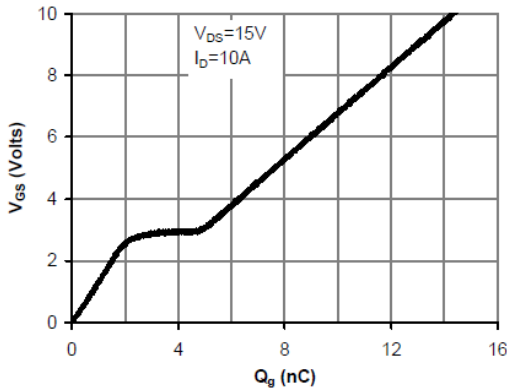
**TYPICAL CHARACTERISTICS**


Figure 7: Gate-Charge Characteristics

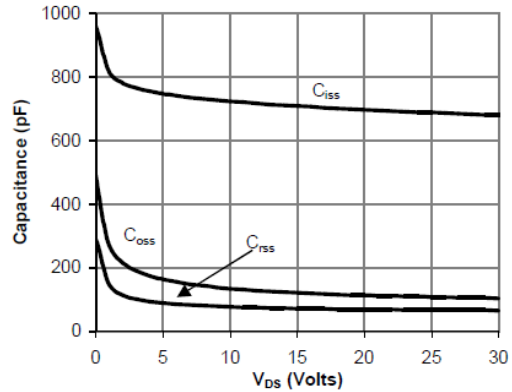


Figure 8: Capacitance Characteristics

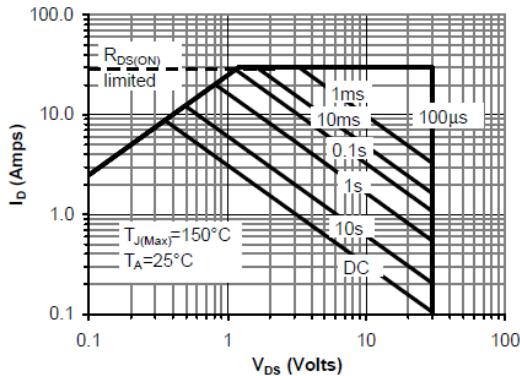


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

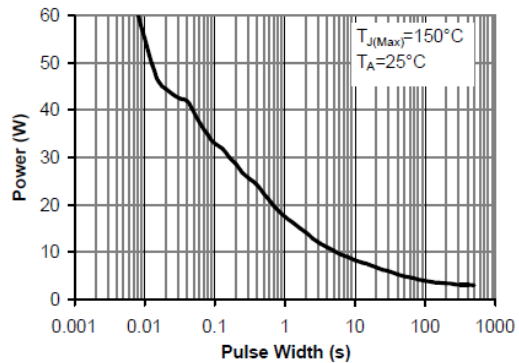


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

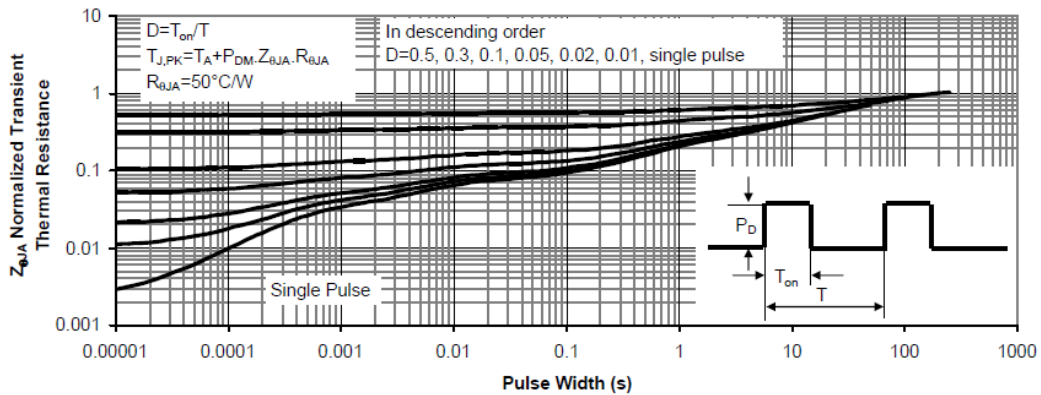
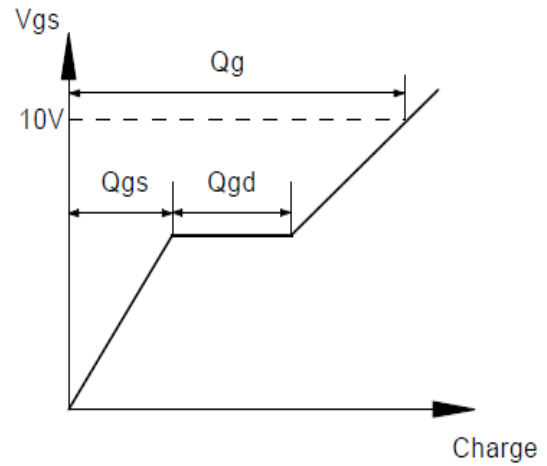
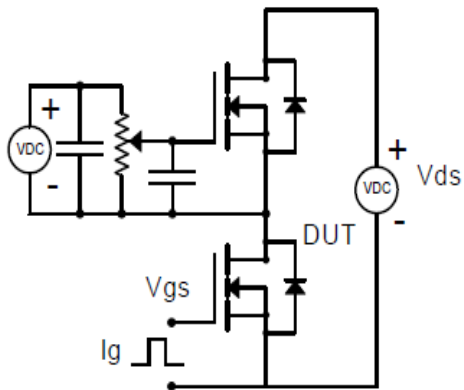
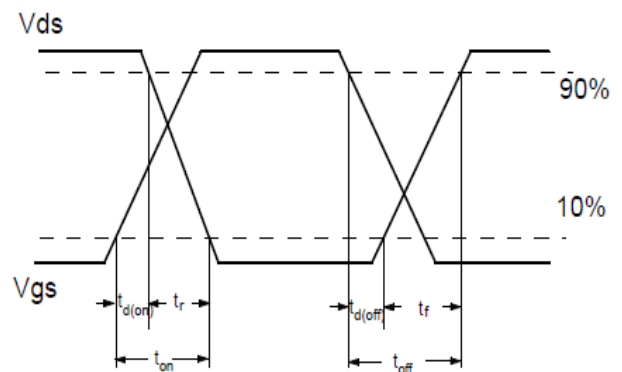
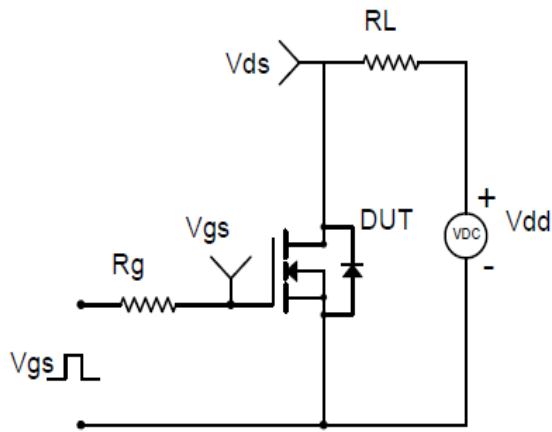


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

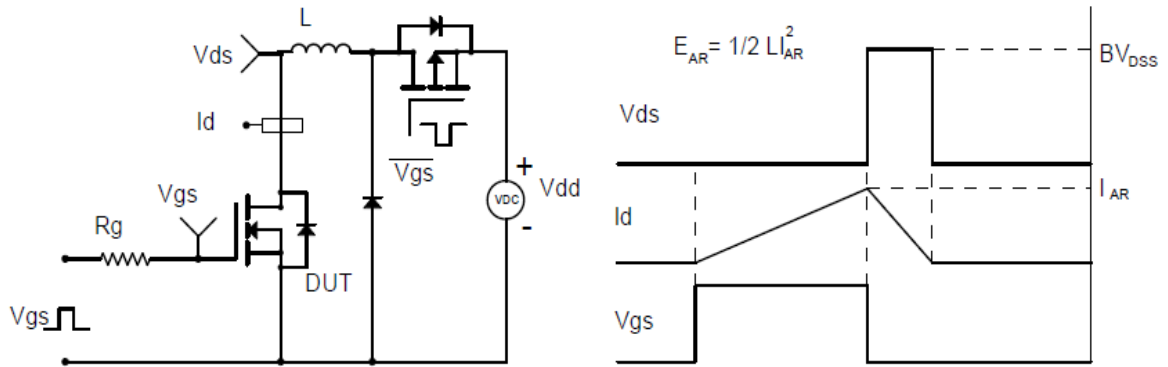
Gate Charge Test Circuit & Waveform



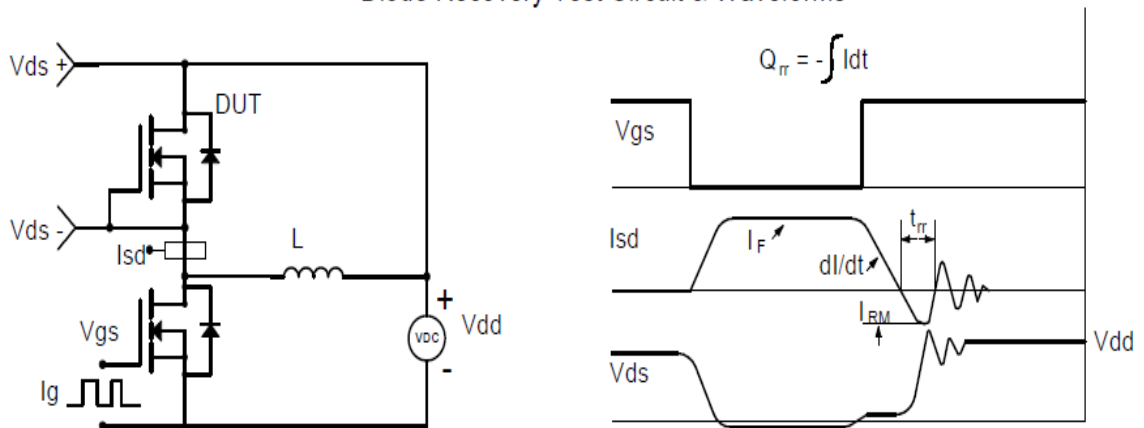
Resistive Switching Test Circuit & Waveforms

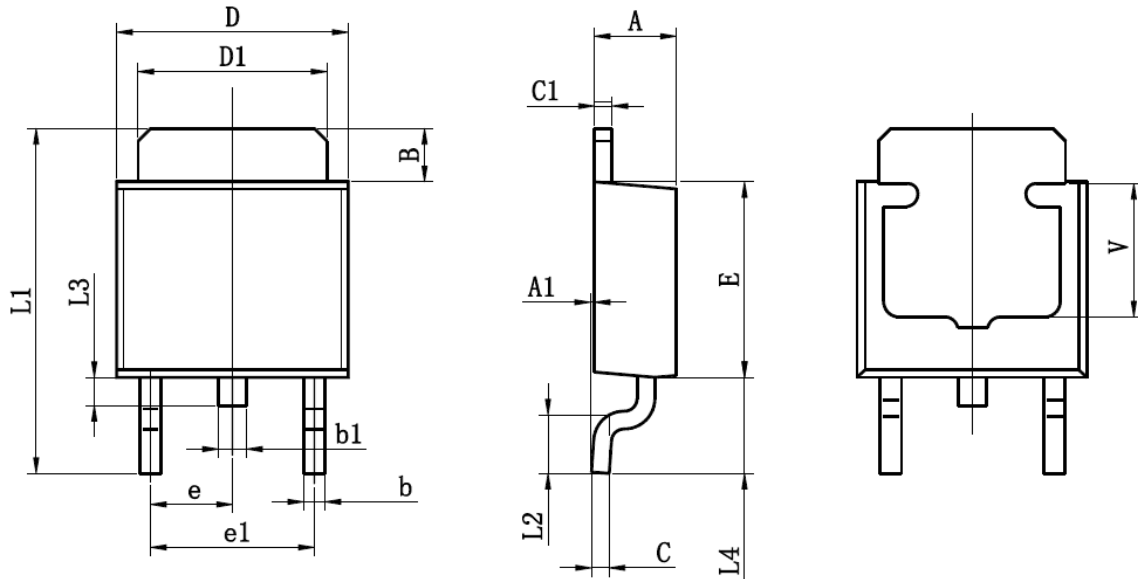


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



**TO-252-2L PACKAGE OUTLINE SOP-8P**


| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 2.200                     | 2.400 | 0.087                | 0.094 |
| A1     | 0.000                     | 0.127 | 0.000                | 0.005 |
| B      | 1.350                     | 1.650 | 0.053                | 0.065 |
| b      | 0.500                     | 0.700 | 0.020                | 0.028 |
| b1     | 0.700                     | 0.900 | 0.028                | 0.035 |
| c      | 0.430                     | 0.580 | 0.017                | 0.023 |
| c1     | 0.430                     | 0.580 | 0.017                | 0.023 |
| D      | 6.350                     | 6.650 | 0.250                | 0.262 |
| D1     | 5.200                     | 5.400 | 0.205                | 0.213 |
| E      | 5.400                     | 5.700 | 0.213                | 0.224 |
| e      | 2.300TYP                  |       | 0.091TYP             |       |
| e1     | 4.500                     | 4.700 | 0.177                | 0.185 |
| L1     | 9.500                     | 9.900 | 0.374                | 0.390 |
| L2     | 1.400                     | 1.780 | 0.055                | 0.070 |
| L3     | 0.650                     | 0.950 | 0.026                | 0.037 |
| L4     | 2.550                     | 2.900 | 0.100                | 0.114 |
| V      | 3.80REF                   |       | 0.150REF             |       |